

U.S. PTO  
10/034379



305/579

# U.S. UTILITY Patent Application

PATENT NUMBER and  
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10034379	01/03/2002	438	770	2812	D. NHU

\*\*APPLICANTS: Tsurugida Yoshirou;

\*\*CONTINUING DATA VERIFIED:

NONE

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\*\* FOREIGN APPLICATIONS VERIFIED:

JAPAN 286030/2001 09/20/2001

PG-PUB DO NOT PUBLISH ☐

RESCIND ☐

Foreign priority claimed ☒ yes ☐ no

35 USC 119 conditions met ☒ yes ☐ no

Verifert and Acknowledged Examiners's initials *or*

ATTORNEY DOCKET NO

OKI.291

TITLE : Method for selectively oxidizing a silicon wafer

U.S. DEPT. OF COMM / PAT. & TM. PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
3/27/03		Total Claims <input checked="" type="checkbox"/>	Print Claim for O.G. 1
ISSUE FEE		DRAWING	
Amount Due 1600	Date Paid	Sheets Drwg. 2	Figs. Drwg. 5
		Print Fig. 1E	
<input type="checkbox"/> TERMINAL DISCLAIMER		Application Examiner J. Johnson 3/27/03	
		PREPARED FOR ISSUE	
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